#### **ABSOLUTE MAXIMUM RATINGS**

(Voltages Referenced to GND)	Co
V+0.3V to +44.0V	P
V44.0V to +0.3V	N
V+ to V0.3V to +44.0V	T
COM_, IN_ (Note 1)(V 0.3V) to (V+ + 0.3V)	C
NC_, NO_ (Note 2)(V+ - 36V) to (V- + 36V)	Ор
NC_, NO_ to COM36V to +36V	N
Continuous Current into Any Terminal±30mA	Λ
Peak Current into Any Terminal	N
(pulsed at 1ms, 10% duty cycle)±50mA	Sto

Continuous Power Dissipation (T <sub>A</sub> = +70°C)	(Note 2)
Plastic DIP (derate 10.53mW/°C above +7	'0°C)842mW
Narrow SO (derate 8.70mW/°C above +70	)°C)696mW
TSSOP (derate 9.4mW/°C above +70°C).	754.7mW
CERDIP (derate 10.00mW/°C above +70°C	C)800mW
Operating Temperature Ranges	
MAX451_C_ E	0°C to +70°C
MAX451_E_ E	40°C to +85°C
MAX451_MJE	55°C to +125°C
Storage Temperature Range	65°C to +150°C
Lead Temperature (soldering, 10s)	+300°C

- Note 1: COM\_ and IN\_ pins are not fault protected. Signals on COM\_ or IN\_ exceeding V+ or V- are clamped by internal diodes. Limit forward diode current to maximum current rating.
- Note 2: NC\_ and NO\_ pins are fault protected. Signals on NC\_ or NO\_ exceeding -36V to +36V may damage the device. These limits apply with power applied to V+ or V-, or ±40V with V+ = V- = 0.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### **ELECTRICAL CHARACTERISTICS—Dual Supplies**

 $(V+ = +15V, V- = -15V, GND = 0V, T_A = T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted.}$  Typical values are at  $T_A = +25^{\circ}C.)$ 

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP (Note 3)	MAX	UNITS	
ANALOG SWITCH			1					
Fault-Protected Analog Signal Range	V <sub>NO_</sub> , V <sub>NC_</sub>	Applies with power on or off (Note 2)	C, E, M	-36		36	V	
Fault-Free Analog Signal Range	V <sub>NO_</sub> , V <sub>NC_</sub>	Applies with power on or off (Note 2)	C, E, M	V-		V+	V	
Non-Protected Analog Signal Range (COM_ Output)	VCOM_	Applies with power on or off (Note 1)	C, E, M	V 0.3	}	V+ + 0.3	V	
0014 NO 0014 NO			+25°C		125	160		
COMNO_ or COMNC_ On-Resistance	Ron	V <sub>COM</sub> _ = ±10V, I <sub>COM</sub> _ = 1mA	C, E			200	Ω	
On Modistance			М			250	1	
COMNO_ or COMNC_			+25°C		3	6		
On-Resistance Match Between	$\Delta R_{ON}$	$V_{COM} = \pm 10V$ , $I_{COM} = 1mA$	C, E			10	Ω	
Channels (Note 4)	ote 4)	ieis (Note 4)		М			15	
NO or NO Off Lookage Current		\/aa	+25°C	-0.5	0.01	0.5		
NO_ or NC_ Off Leakage Current (Note 5)	INO_(OFF), INC_(OFF)	$V_{COM} = \pm 14V;$ $V_{NO}, V_{COM} = \pm 14V$	C, E	-10		10	nA	
(	.110_(011)	110_, 100W + 111	М	-200		200		
00M 0#1l 0		V	+25°C	-0.5	0.01	0.5		
COM_ Off Leakage Current (Note 5)	I <sub>COM_(OFF)</sub>	$V_{COM} = \pm 14V;$ $V_{NO}, V_{COM} = \pm 14V$	C, E	-10		10	nA	
(11010 0)	VNO_, VCOM = + 14V	М	-200		200			
COM On London Com.			+25°C	-0.5	0.01	0.5		
COM_ On Leakage Current (Note 5)	ICOM_(ON)	$V_{COM} = \pm 14V$	C, E	-20		20	nA	
(Note 5)			М	-400		400	1	

### **ELECTRICAL CHARACTERISTICS—Dual Supplies (continued)**

(V+ = +15V, V- = -15V, GND = 0V,  $T_A = T_{MIN}$  to  $T_{MAX}$ , unless otherwise noted. Typical values are at  $T_A = +25$ °C.)

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP (Note 3)	MAX	UNITS
<b>FAULT</b> (V+ = +15V, V- = -15V, un	less otherwise no	oted.)					
			+25°C	-10		10	nA
COM_ Output Leakage Current, Supplies On	ICOM_	$V_{NO}$ or $V_{NC} = \pm 33V$	C, E	-200		200	
			М	-1		1	μA
NO NO 0"1 1		V V 051/	+25°C	-20		20	nA
NO_ or NC_ Off Input Leakage Current, Supplies On	I <sub>NO_</sub> , I <sub>NC_</sub>	$I_{NO_{-}}, I_{NC_{-}}$ $V_{NO_{-}}$ or $V_{NC_{-}} = \pm 25V$ , $V_{COM_{-}} = \mp 10V$	C, E	-200		200	7 114
Garrent, Gappines Off		VCOM_ = + 10V	М	-10		10	μΑ
		., ., .,	+25°C	-20	0.1	20	
NO_ or NC_ Input Leakage Current, Supplies Off	I <sub>NO_</sub> , I <sub>NC_</sub>	$V_{NO}$ or $V_{NC}$ = ±40V, V+ = 0, V- = 0	C, E	-200		200	– nA
Current, Supplies On		V+ = 0, V- = 0	М	-10		10	μA
COM On Output Current,		V <sub>NO</sub> _ or V <sub>NC</sub> _ = 33V	2500	8	11	13	
Supplies On	ICOM_	V <sub>NO</sub> or V <sub>NC</sub> = -33V	+25°C	-12	-10	-7	mA
COM On Output Resistance,		_	+25°C		1	2.5	
Supplies On	RCOM_	$V_{NO}$ or $V_{NC}$ = ±33 $V$	C, E, M			3	kΩ
LOGIC INPUT							
IN_ Input Logic Threshold High	V <sub>IN_</sub> H		C, E, M		1.9	2.4	V
IN_ Input Logic Threshold Low	V <sub>IN_L</sub>		C, E, M	0.8	1.9		V
IN_ Input Current Logic High			+25°C	-1	0.03	1	
or Low	I <sub>INH</sub> _, I <sub>INL</sub>	$V_{IN} = 0.8V \text{ or } 2.4V$	C, E, M	-5		5	μΑ
SWITCH DYNAMIC CHARACTER	RISTICS						
			+25°C		350	500	
Turn-On Time	ton	$V_{COM} = \pm 10V, R_L = 2k\Omega,$	C, E			600	ns
	0.1	Figure 2	M			900	-
			+25°C		200	400	
Turn-Off Time	toff	$V_{COM} = \pm 10V, R_L = 2k\Omega,$	C, E			500	ns
	-011	Figure 2	M			750	-
Break-Before-Make Time Delay (MAX4513 Only)	tBBM	$V_{COM} = \pm 10V, R_{L} = 2k\Omega,$ Figure 3	+25°C	50	100		ns
Charge Injection (Note 6)	Q	$C_L = 1.0$ nF, $V_{NO} = 0$ , $R_S = 0\Omega$ , Figure 4	+25°C		1.5	5	рС
NO_ or NC_ Off-Capacitance	C <sub>N</sub> (OFF)	f = 1MHz, Figure 5	+25°C		10		pF
COM_ Off-Capacitance	CCOM_(OFF)	f = 1MHz, Figure 5	+25°C		5		pF
COM_ On-Capacitance	CCOM_(ON)	f = 1MHz, Figure 5	+25°C		10		pF
Off Isolation (Note 7)	VCISO	$R_L = 50\Omega$ , $C_L = 15pF$ , $V_{N} = 1V_{RMS}$ , $f = 1MHz$ , Figure 6	+25°C		-62		dB
Channel-to-Channel Crosstalk (Note 9)	V <sub>CT</sub>	$R_L = 50\Omega$ , $C_L = 15pF$ , $V_{N} = 1V_{RMS}$ , $f = 1MHz$ , Figure 6	+25°C		-66		dB

### **ELECTRICAL CHARACTERISTICS—Dual Supplies (continued)**

(V+ = +15V, V- = -15V, GND = 0V,  $T_A = T_{MIN}$  to  $T_{MAX}$ , unless otherwise noted. Typical values are at  $T_A = +25$ °C.)

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP (Note 3	MAX )	UNITS	
POWER SUPPLY								
Power-Supply Range	V+, V-		C,E, M	±4.5		±18	V	
V. Supply Current	I+	All $V_{IN} = 0$ or $5V$	+25°C		280	400		
V+ Supply Current	1+	All V[N] = 0 01 3V	C, E, M			600	μA	
V Supply Current		+2	+25°C		90	200		
V- Supply Current	I-	I- All $V_{IN} = 0$ or 5V	C, E, N	C, E, M			300	- μΑ
		AU. / 0 - :: 45 / /	+25°C	-1	0.01	1		
GND Supply Current I <sub>GND</sub>	All $V_{IN} = 0$ or 15V	C, E, M			10	μA		
	ΛΙΙ. \/(x) =	+25°C		150	250			
		All V <sub>IN</sub> _ = 5V	C, E, M			450	- μΑ	

### **ELECTRICAL CHARACTERISTICS—Single +12V Supply**

 $(V+=+10.8V \text{ to } +13.2V, V-=0, T_A=T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted. Typical values are at } T_A=+25^{\circ}C.)$ 

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP (Note 3	MAX B)	UNITS	
ANALOG SWITCH		1						
Fault-Protected Analog Signal Range	V <sub>NO</sub> _, V <sub>NC</sub> _	Applies with power on or off (Note 2)	C, E, M	-36		36	V	
Fault-Free Analog Signal Range	V <sub>NO</sub> _, V <sub>NC</sub> _	Applies with power on or off (Note 2)	C, E, M	0		V+	V	
Non-Protected Analog Signal Range (COM_ Output)	VCOM_	Applies with power on or off (Note 1)	C, E, M	-0.3		V+ + 0.3	V	
0014 110 0014 110		101/1/	+25°C		260	390		
COMNO_ or COMNC_ On-Resistance	RON	$V + = 12V, V_{COM} = 10V,$ $I_{COM} = 1mA$	C, E			450	Ω	
On resistance		ICOM_ = ITTIV	М			525	1	
COMNO_ or COMNC_		101/1/	+25°C		4	10		
On-Resistance Match Between	$\Delta Ron$	$V+ = 12V, V_{COM} = 10V,$ $I_{COM} = 1mA$	C, E			20	Ω	
Channels (Note 4)		ICOM_ = ITTIV	М			30	1	
NO NO 0"1 1 0	r NC_ Off Leakage Current   I <sub>ON_(OFF)</sub> ,   V+ = 12V; V <sub>COM_</sub> = 10V   V <sub>NO_</sub> , V <sub>NC</sub> = 0 or 12V	101/1/	+25°C	-0.5	0.01	0.5		
NO_ or NC_ Off Leakage Current (Notes 5, 9)			C, E	-10		10	nA	
(Notes 3, 9)		VNO_, VNC = 0 01 12V	М	-200		200	1	
			+25°C	-0.5	0.01	0.5	.5	
COM_ Off Leakage Current (Notes 5, 9)	ICOM_(OFF)	$V + = 12V; V_{COM} = 0;$ $V_{NO}, V_{NC} = 12V$	C, E	-10		10	nA	
(Notes 5, 9)		VNO_, VNC_ = 12V	М	-200		200	1	
				+25°C	-0.5	0.01	0.5	
COM_ On Leakage Current (Notes 5, 9)		V+ = 12V, $V_{COM} = 10V \text{ or } 12V$	C, E	-20		20	nA	
(Notes 5, 9)		VCOM_ = 10V 01 12V	М	-400		400	1	
FAULT			· ·					
			+25°C	-10		10	A	
COM_ Output Leakage Current, Supply On	I <sub>COM</sub> _	$V_{NO}$ or $V_{NC} = \pm 30V$ , $V_{+} = 12V$	C, E	-200		200	nA	
Ситепі, Зирріу Оп		V+ = 12V	М	-1		1	μΑ	
			+25°C	-20		20	A	
NO_ or NC_ Off Input Leakage Current, Supply On	I <sub>NO_</sub> , I <sub>NC_</sub>	$V_{NO}$ or $V_{NC}$ = ±25V, $V_{COM}$ = 0, V+ = 12V	C, E	-200		200	nA	
Current, Supply On		VCOM_ = 0, V+ = 12V	М	-10		10	μΑ	
			+25°C	-20	0.1	20	A	
NO_ or NC_ Input Leakage Current, Supply Off			C, E	-200		200	nA	
оштепі, опрріу Оп		v + - 0, v 0	М	-10		10	μA	
COM_ Output Current, Supply On	ICOM_	$V_{NO_{-}}$ or $V_{NC_{-}} = 25V$ , V+ = 12V	+25°C	2	3	5	mA	
COM_ Output Resistance, Supply On	R <sub>COM</sub> _	V <sub>NO_</sub> or V <sub>NC_</sub> = 10V V+ = 12V	+25°C		2.4	5	kΩ	

### **ELECTRICAL CHARACTERISTICS—Single +12V Supply (continued)**

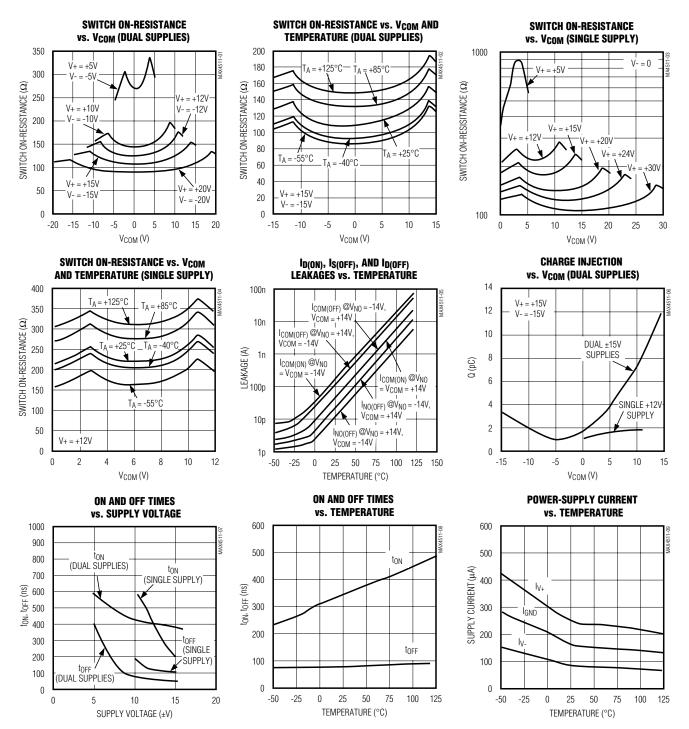
 $(V+ = +10.8V \text{ to } +13.2V, V- = 0, T_A = T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted.}$  Typical values are at  $T_A = +25^{\circ}\text{C.})$ 

PARAMETER	SYMBOL	CONDITIONS	TA	MIN	TYP (Note 3)	MAX	UNITS
LOGIC INPUT							
IN_ Input Logic Threshold High	V <sub>IN_H</sub>		C, E, M		1.8	2.4	V
IN_ Input Logic Threshold Low	V <sub>IN_L</sub>		C, E, M	0.8	1.8		V
IN_ Input Current Logic High or Low	lin_H, lin_L	V <sub>IN</sub> _ = 0.8V or 2.4V	+25°C C, E, M	-1 -5	0.03	1 5	μA
SWITCH DYNAMIC CHARACTE	RISTICS		O, L, W				
		$V_{COM} = 10V, R_L = 2k\Omega,$	+25°C		500	1000	
Turn-On Time	ton	Figure 2	C, E, M			1500	ns
		$V_{COM} = 10V, R_L = 2k\Omega,$	+25°C		400	900	
Turn-Off Time	toff	Figure 2	C, E, M			1200	ns
Break-Before-Make Time Delay (MAX4513 Only)	tBBM	$V_{COM}$ = 10V, $R_{L}$ = 2k $\Omega$ , Figure 3	+25°C	50	100		ns
Charge Injection (Note 6)	Q	$C_L = 1.0$ nF, $V_{NO} = 0$ , $R_S = 0\Omega$ , Figure 4	+25°C		1	5	рС
NO_ or NC_ Off Capacitance	C <sub>N_</sub> (OFF)	f = 1MHz, Figure 5	+25°C		9		pF
COM_ Off Capacitance	CCOM_ (OFF)	V <sub>COM</sub> _ = GND, f = 1MHz, Figure 5	+25°C		9		pF
COM_ On Capacitance	C <sub>COM</sub> _(ON)	V <sub>COM</sub> _ = V <sub>NO</sub> _ = GND, f = 1MHz, Figure 5	+25°C		22		pF
Off Isolation (Note 7)	V <sub>ISO</sub>	$R_L = 50\Omega$ , $C_L = 15pF$ , $V_{N} = 1V_{RMS}$ , $f = 1MHz$ , Figure 6	+25°C		-62		dB
Channel-to-Channel Crosstalk (Note 8)	VCT	$R_L = 50\Omega$ , $C_L = 15pF$ , $V_{N} = 1V_{RMS}$ , $f = 1MHz$ , Figure 5	+25°C		-65		dB
POWER SUPPLY	1						1
Power-Supply Range	V+		C,E, M	9		36	V
V+ Supply Current	l+	All V <sub>IN</sub> _ = 0 or 5V	+25°C		150	300	μΑ
v – Зарріў Сапепі	I T	All viiv_ = 0 0i 3v	C, E, M			450	μΑ
		All V <sub>IN</sub> _ = 0 or 12V	+25°C		50	100	
V- and GND Supply Current	I <sub>GND</sub>	/ W V       -	C, E, M			200	μA
v and divid dupply durient	IGND	All V <sub>IN</sub> = 5V	+25°C		150	300	
		, v <sub>IIV</sub> _ – 5 v	C, E, M			450	

- Note 1: COM\_ and IN\_ pins are not fault protected. Signals on COM\_ or IN\_ exceeding V+ or V- are clamped by internal diodes. Limit forward diode current to maximum current rating.
- Note 2: NC\_ and NO\_ pins are fault protected. Signals on NC\_ or NO\_ exceeding -36V to +36V may damage the device. These limits apply with power applied to V+ or V-, or ±40V with V+ = V- = 0.
- Note 3: The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.
- **Note 4:**  $\Delta R_{ON} = \Delta R_{ON(MAX)} \Delta R_{ON(MIN)}$ .
- Note 5: Leakage parameters are 100% tested at maximum rated hot temperature and guaranteed by correlation at TA = +25°C.
- Note 6: Guaranteed by design.
- Note 7: Off isolation = 20 log10 [ V<sub>COM\_</sub> / (V<sub>NC\_</sub> or V<sub>NO\_</sub>)], V<sub>COM\_</sub> = output, V<sub>NC\_</sub> or V<sub>NO\_</sub> = input to off switch.
- Note 8: Between any two switches.
- Note 9: Leakage testing for single-supply operation is guaranteed by testing with dual supplies.

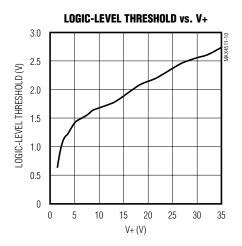
### **Typical Operating Characteristics**

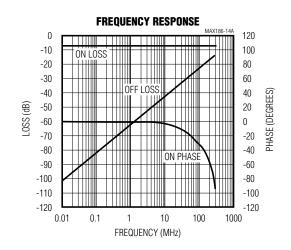
 $(T_A = +25^{\circ}C, \text{ unless otherwise noted.})$ 



### \_Typical Operating Characteristics (continued)

 $(T_A = +25^{\circ}C, \text{ unless otherwise noted.})$ 





### **Pin Description**

PIN	NAME	FUNCTION
1, 16, 9, 8	IN1-IN4	Logic Control Digital Inputs
2, 15, 10, 7	COM1- COM4	Analog Switch Common* Terminals
3, 14, 11, 6	NO1-NO4 or NC1-NC4	Analog Switch Fault-Protected Normally Open* or Normally Closed* Terminals
4	V-	Negative Analog Supply Voltage Input. Connect to GND for single-supply operation.
5	GND	Ground. Connect to digital ground. (Analog signals have no ground reference.)
12	N.C.	No Connection—not internally connected
13	V+	Positive Analog and Digital Supply-Voltage Input. Internally connected to substrate.

<sup>\*</sup>As long as the voltage on NO\_ or NC\_ does not exceed V+ or V-, NO\_ (or NC\_) and COM\_ pins are identical and interchangeable. Either may be considered as an input or output; signals pass equally well in either direction.

### Detailed Description

#### Overview of Traditional Fault-Protected Switches

The MAX4511/MAX4512/MAX4513 are fault-protected CMOS analog switches with unusual operation and construction. Traditional fault-protected switches are constructed by three series FETs. This produces good off characteristics, but fairly high on-resistance when the signals are within about 3V of each supply rail. As the voltage on one side of the switch approaches within about 3V of either supply rail (a fault condition), the switch impedance becomes higher, limiting the output signal range (on the protected side of the switch) to approximately 3V less than the appropriate polarity supply voltage.

During a fault condition, the output current that flows from the protected side of the switch into its load comes from the fault source on the other side of the switch. If the switch is open or the load is extremely high impedance, the input current will be very low. If the switch is on and the load is low impedance, enough current will flow from the source to maintain the load voltage at 3V less than the supply.

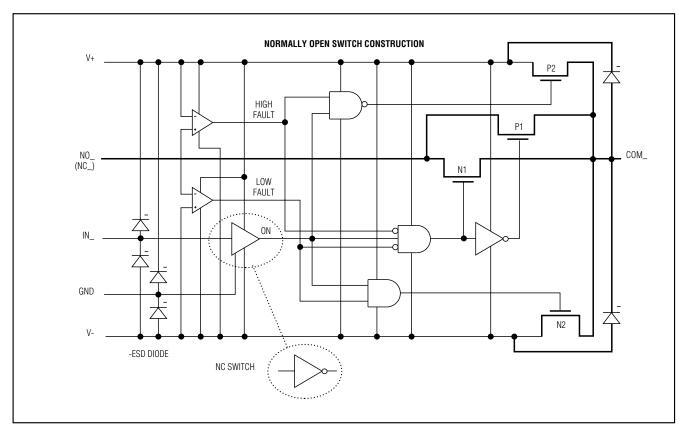


Figure 1. Block Diagram

#### Overview of MAX4511/MAX4512/MAX4513

The MAX4511/MAX4512/MAX4513 differ considerably from traditional fault-protection switches, with several advantages. First, they are constructed with two parallel FETs, allowing very low on-resistance when the switch is on. Second, they allow signals on the NC\_ or NO\_ pins that are within or slightly beyond the supply rails to be passed through the switch to the COM terminal, allowing rail-to-rail signal operation. Third, when a signal on NC\_ or NO\_ exceeds the supply rails by about 50mV (a fault condition), the voltage on COM\_ is limited to the appropriate polarity supply voltage. Operation is identical for both fault polarities. The fault-protection extends to ±36V from GND.

During a fault condition, the NO\_ or NC\_ input pin becomes high impedance regardless of the switch state or load resistance. If the switch is on, the COM\_ output current is furnished from the V+ or V- pin by "booster" FETs connected to each supply pin. These FETs can typically source or sink up to 10mA.

When power is removed, the fault protection is still in effect. In this case, the NO\_ or NC\_ terminals are a virtual open circuit. The fault can be up to  $\pm 40$ V.

The COM\_ pins are not fault protected; they act as normal CMOS switch pins. If a voltage source is connected to any COM\_ pin, it should be limited to the supply voltages. Exceeding the supply voltage will cause high currents to flow through the ESD protection diodes, possibly damaging the device (see *Absolute Maximum Ratings*).

#### Pin Compatibility

These switches have identical pinouts to common non-fault-protected CMOS switches. Care should be exercised in considering them for direct replacements in existing printed circuit boards, however, since only the NO\_ and NC\_ pins of each switch are fault protected.

#### **Internal Construction**

Internal construction is shown in Figure 1, with the analog signal paths shown in bold. A single normally open

(NO) switch is shown; the normally closed (NC) configuration is identical except the logic-level translator becomes an inverter. The analog switch is formed by the parallel combination of N-channel FET N1 and P-channel FET P1, which are driven on and off simultaneously according to the input fault condition and the logic-level state.

#### **Normal Operation**

Two comparators continuously compare the voltage on the NO\_ (or NC\_) pin with V+ and V-. When the signal on NO\_ or NC\_ is between V+ and V- the switch acts normally, with FETs N1 and P1 turning on and off in response to IN\_ signals. The parallel combination of N1 and P1 forms a low-value resistor between NO\_ (or NC\_) and COM\_ so that signals pass equally well in either direction.

#### **Positive Fault Condition**

When the signal on NO\_ (or NC\_) exceeds V+ by about 50mV, the high-fault comparator output is high, turning off FETs N1 and P1. This makes the NO\_ (or NC\_) pin high impedance regardless of the switch state. If the switch state is "off", all FETs are turned off and both NO\_ (or NC\_) and COM\_ are high impedance. If the switch state is "on", FET P2 is turned on, sourcing current from V+ to COM\_.

#### **Negative Fault Condition**

When the signal on NO\_ (or NC\_) exceeds V- by about 50mV, the low-fault comparator output is high, turning off FETs N1 and P1. This makes the NO\_ (or NC\_) pin high impedance regardless of the switch state. If the switch state is "off," all FETs are turned off and both NO\_ (or NC\_) and COM\_ are high impedance. If the switch state is "on," FET N2 is turned on, sinking current from COM\_ to V-.

#### **Transient Fault Response and Recovery**

When a fast rise-time and fall-time transient on IN\_exceeds V+ or V-, the output (COM\_) follows the input (IN\_) to the supply rail with only a few nanoseconds delay. This delay is due to the switch on-resistance and circuit capacitance to ground. When the input transient returns to within the supply rails, however, there is a longer output recovery time delay. For positive faults, the recovery time is typically 3.5µs. For negative faults, the recovery time is typically 1.3µs. These values depend on the COM\_ output resistance and capacitance, and are not production tested or guaranteed. The delays are not dependent on the fault amplitude. Higher COM\_ output resistance and capacitance increase recovery times.

#### **COM and IN Pins**

FETs N2 and P2 can source about ±10mA from V+ or V-to the COM\_ pin in the fault condition. Ensure that if the COM\_ pin is connected to a low-resistance load, the absolute maximum current rating of 30mA is never exceeded, both in normal and fault conditions.

The GND, COM\_, and IN\_ pins do not have fault protection. Reverse ESD-protection diodes are internally connected between GND, COM\_, IN\_ and both V+ and V-. If a signal on GND, COM\_, or IN\_ exceeds V+ or V- by more than 300mV, one of these diodes will conduct heavily. During normal operation these reverse-biased ESD diodes leak a few nanoamps of current to V+ and V-.

#### Fault-Protection Voltage and Power Off

The maximum fault voltage on the NC\_ or NO\_ pins is ±36V with power applied and ±40V with power off.

#### **Failure Modes**

The MAX4511/MAX4512/MAX4513 are not lightning arrestors or surge protectors.

Exceeding the fault-protection voltage limits on NO\_ or NC\_, even for very short periods, can cause the device to fail. The failure modes may not be obvious, and failure in one switch may or may not affect other switches in the same package.

#### Ground

There is no connection between the analog signal paths and GND. The analog signal paths consist of an N-channel and P-channel MOSFET with their sources and drains paralleled and their gates driven out of phase to V+ and V- by the logic-level translators.

V+ and GND power the internal logic and logic-level translators and set the input logic thresholds. The logic-level translators convert the logic levels to switched V+ and V- signals to drive the gates of the analog switches. This drive signal is the only connection between the power supplies and the analog signals. GND, IN\_, and COM\_ have ESD-protection diodes to V+ and V-.

#### IN\_ Logic-Level Thresholds

The logic-level thresholds are CMOS and TTL compatible when V+ is +15V. As V+ is raised the threshold increases slightly, and when V+ reaches 25V the level threshold is about 2.8V—above the TTL output high level minimum of 2.4V, but still compatible with CMOS outputs (see *Typical Operating Characteristics*).

Increasing V- has no effect on the logic-level thresholds, but it does increase the gate-drive voltage to the signal FETs, reducing their on-resistance.

#### **Bipolar Supplies**

The MAX4511/MAX4512/MAX4513 operate with bipolar supplies between ±4.5V and ±18V. The V+ and V- supplies need not be symmetrical, but their difference can not exceed the absolute maximum rating of 44V.

#### **Single Supply**

The MAX4511/MAX4512/MAX4513 operate from a single supply between +9V and +36V when V- is connected to GND.

#### High-Frequency Performance

In  $50\Omega$  systems, signal response is reasonably flat up to 50MHz (see *Typical Operating Characteristics*). Above

20MHz, the on-response has several minor peaks that are highly layout dependent. The problem with high-frequency operation is not turning the switch on, but turning it off. The off-state switch acts like a capacitor and passes higher frequencies with less attenuation. At 10MHz, off isolation is about -42dB in  $50\Omega$  systems, becoming worse (approximately 20dB per decade) as frequency increases. Higher circuit impedances also make off isolation worse. Adjacent channel attenuation is about 3dB above that of a bare IC socket and is due entirely to capacitive coupling.

### **Test Circuits/Timing Diagrams**

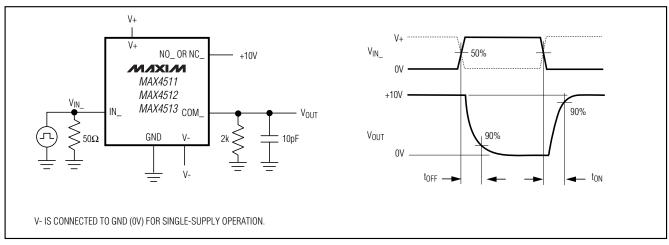


Figure 2. Switch Turn-On/Turn-Off Times

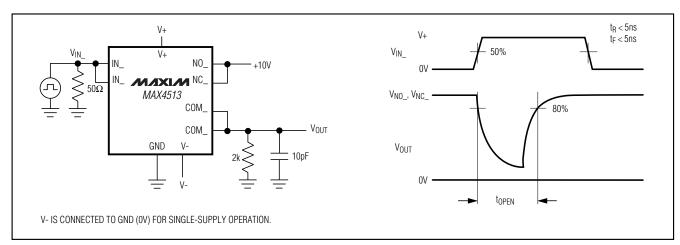


Figure 3. MAX4513 Break-Before-Make Interval

## Test Circuits/Timing Diagrams (continued)

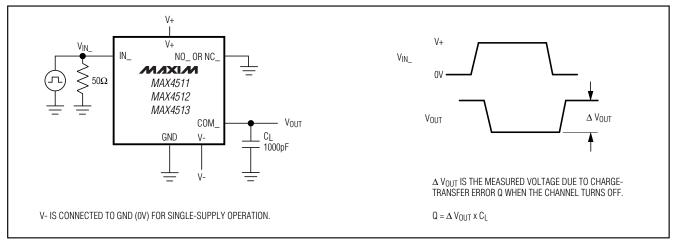


Figure 4. Charge Injection

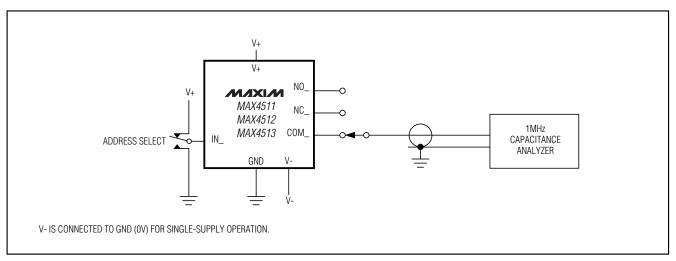


Figure 5. COM\_, NO\_, NC\_ Capacitance

### Test Circuits/Timing Diagrams (continued)

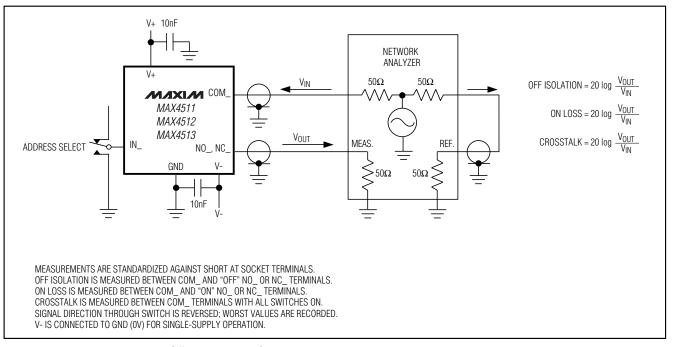
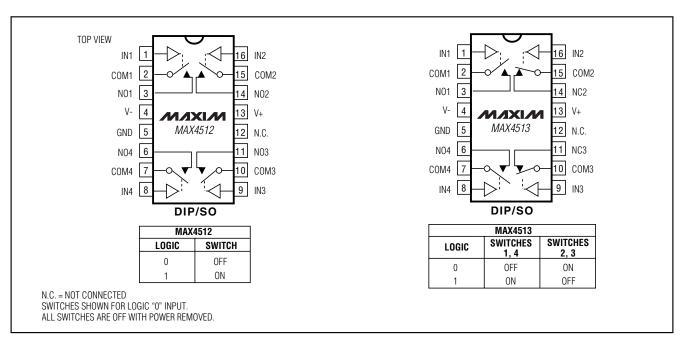


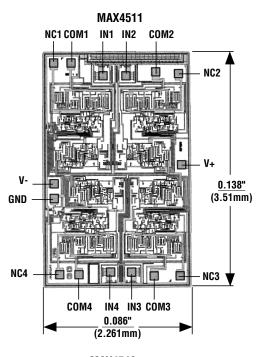
Figure 6. Frequency Response, Off Isolation, and Crosstalk

### Pin Configurations/Functional Diagrams/Truth Tables (continued)



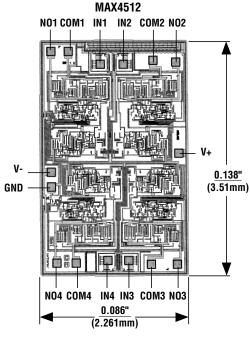
### **Chip Topographies**

### Ordering Information (continued)



Orucinig	momation	(continued)
PART	TEMP RANGE	PIN-PACKAGE
MAX4512CPE	0°C to +70°C	16 Plastic DIP
MAX4512CSE	0°C to +70°C	16 Narrow SO
MAX4512CUE	0°C to +70°C	16 TSSOP
MAX4512C/D	0°C to +70°C	Dice*
MAX4512EPE	-40°C to +85°C	16 Plastic DIP
MAX4512ESE	-40°C to +85°C	16 Narrow SO
MAX4512EUE	-40°C to +85°C	16 TSSOP
MAX4512MJE	-55°C to +125°C	16 CERDIP
MAX4513CPE	0°C to +70°C	16 Plastic DIP
MAX4513CSE	0°C to +70°C	16 Narrow SO
MAX4513CUE	0°C to +70°C	16 TSSOP
MAX4513C/D	0°C to +70°C	Dice*
MAX4513EPE	-40°C to +85°C	16 Plastic DIP
MAX4513ESE	-40°C to +85°C	16 Narrow SO
MAX4513EUE	-40°C to +85°C	16 TSSOP
MAX4513MJE	-55°C to +125°C	16 CERDIP
* Compact footows for	1: :6: 1:	

<sup>\*</sup> Contact factory for dice specifications.



MAX4513
NO1 COM1 IN1 IN2 COM2 NC2

V+
GND

O.138"
(3.51mm)

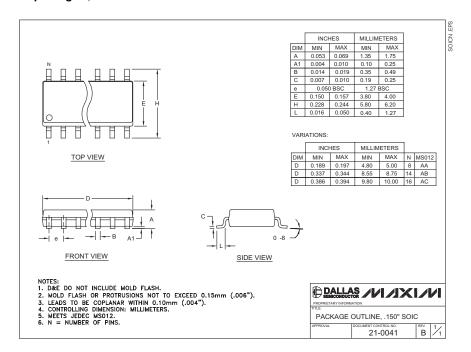
NO4 COM4 IN4 IN3 COM3 NC3

O.086"
(2.261mm)

TRANSISTOR COUNT: 139
SUBSTRATE CONNECTED TO: V+

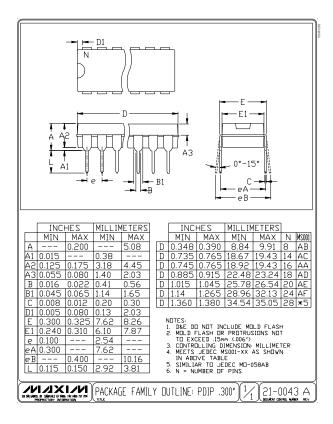
#### Package Information

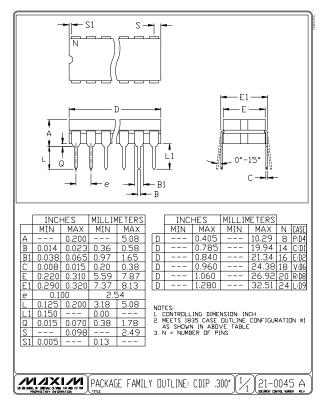
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### Package Information (continued)

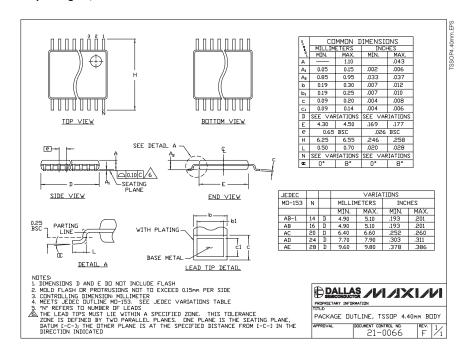
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### Package Information (continued)

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        MAX4511CSE+T
        MAX4511ESE+T
        MAX4512CSE+T

        MAX4512CSE+T
        MAX4512ESE+
        MAX4513CSE+
        MAX4513CSE+T
        MAX4513CSE+T
```